

MOS FIELD EFFECT TRANSISTOR
2SJ243

P-CHANNEL MOS FET
FOR SWITCHING

The 2SJ243 is a P-channel vertical type MOS FET that is driven at 2.5 V.

Because this MOS FET can be driven on a low voltage and because it is not necessary to consider the drive current, the 2SJ243 is ideal for driving the actuator of power-saving systems, such as VCR cameras and headphone stereo systems.

Moreover, the 2SJ243 is housed in a super small mini-mold package so that it can help increase the mounting density on the printed circuit board and lower the mounting cost, contributing to miniaturization of the application systems.

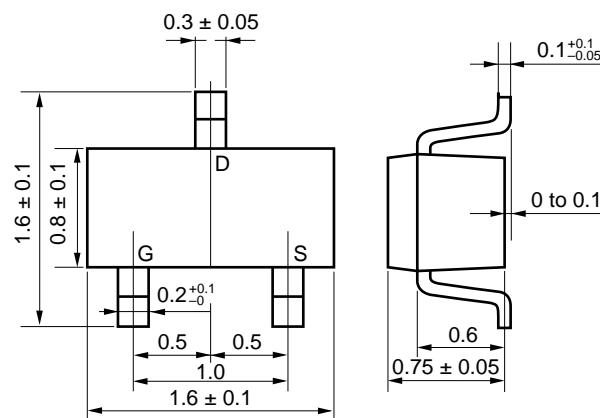
FEATURES

- Small mounting area: about 60 % of the conventional mini-mold package (SC-70)
- Can be directly driven by 3-V IC
- Can be automatically mounted

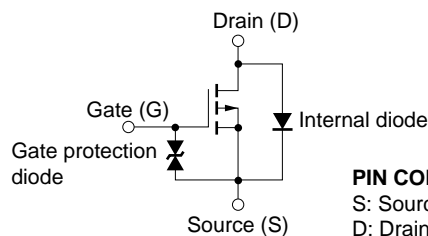
The internal diode in the right figure is a parasitic diode.

The protection diode is to protect the product from damage due to static electricity. If there is a danger that an extremely high voltage will be applied across the gate and source in the actual circuit, a gate protection circuit such as an external constant-voltage diode is necessary.

PACKAGE DIMENSIONS (in mm)



EQUIVALENT CIRCUIT



PIN CONNECTIONS

- S: Source
- D: Drain
- G: Gate

Marking: A1

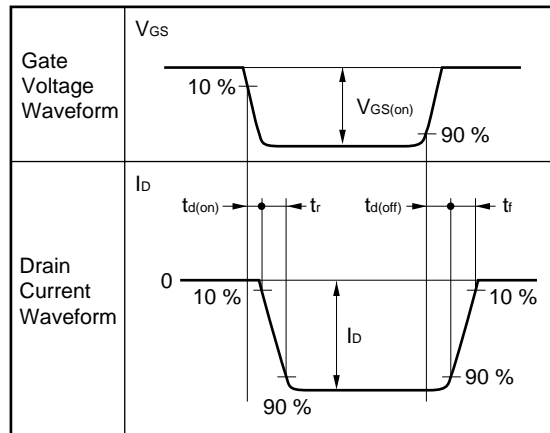
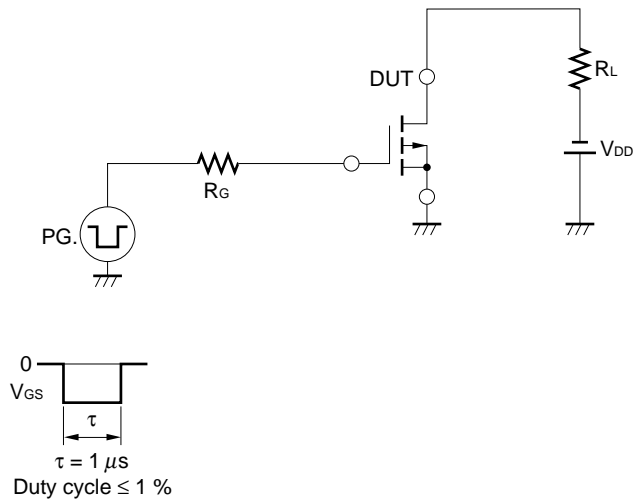
ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C)

PARAMETER	SYMBOL	TEST CONDITIONS	RATING	UNIT
Drain to Source Voltage	V _{DSS}	V _{GS} = 0	-30	V
Gate to Source Voltage	V _{GSS}	V _{DS} = 0	±7	A
Drain Current (DC)	I _{D(DC)}		±100	mA
Drain Current (Pulse)	I _{D(pulse)}	PW ≤ 10 ms Duty cycle ≤ 50 %	±200	mA
Total Power Dissipation	P _T	3.0 cm ² × 0.64 mm, ceramic substrate used	200	mW
Channel Temperature	T _{ch}		150	°C
Operating Temperature	T _{opt}		-55 to +80	°C
Storage Temperature	T _{stg}		-55 to +150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25 °C)

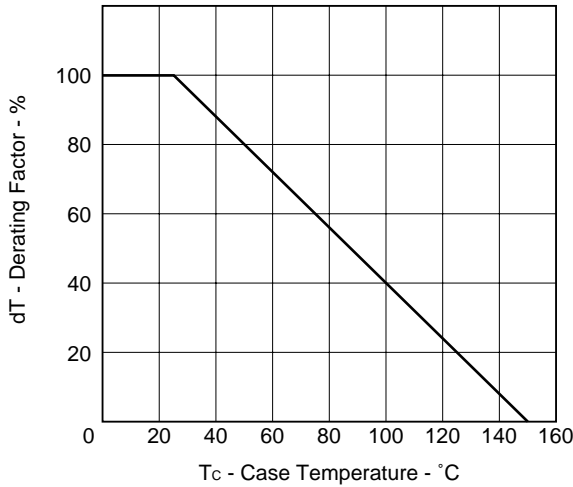
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Drain Cut-Off Current	I _{DSS}	V _{DS} = -30 V, V _{GS} = 0			-1.0	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±5 V, V _{DS} = 0		±0.1	±3.0	μA
Gate Cut-Off Voltage	V _{GS(off)}	V _{DS} = -3 V, I _b = -10 μA	-1.6	-1.9	-2.3	V
Forward Transfer Admittance	y _{ts}	V _{DS} = -3 V, I _b = 10 mA	20	30		mS
Drain to Source On-State Resistance	R _{DS(on)1}	V _{GS} = -2.5 V, I _b = -1 mA		55	100	Ω
Drain to Source On-State Resistance	R _{DS(on)2}	V _{GS} = -4.0 V, I _b = -10 mA		20	25	Ω
Input Capacitance	C _{iss}	V _{DS} = -5.0 V, V _{GS} = 0, f = 1 MHz		16		pF
Output Capacitance	C _{oss}			13		pF
Reverse Transfer Capacitance	C _{rss}			2		pF
Turn-On Delay Time	t _{d(on)}	V _{DD} = -5V, I _b = -10 mA V _{GS(on)} = -5 V, R _G = 10 Ω R _L = 500 Ω		10		ns
Rise Time	t _r			40		ns
Turn-Off Delay Time	t _{d(off)}			130		ns
Fall Time	t _f			80		ns

SWITCHING TIME MEASUREMENT CIRCUIT AND CONDITIONS (Resistive Load)

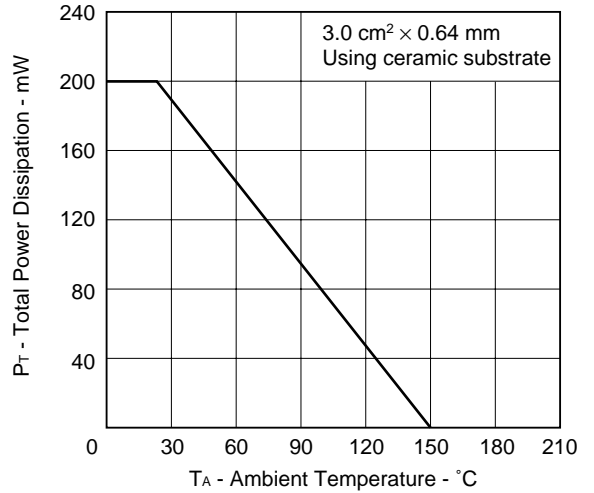


TYPICAL CHARACTERISTICS (T_A = 25 °C)

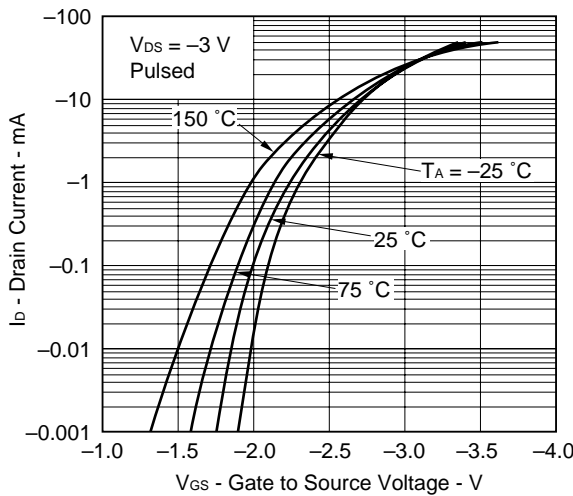
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



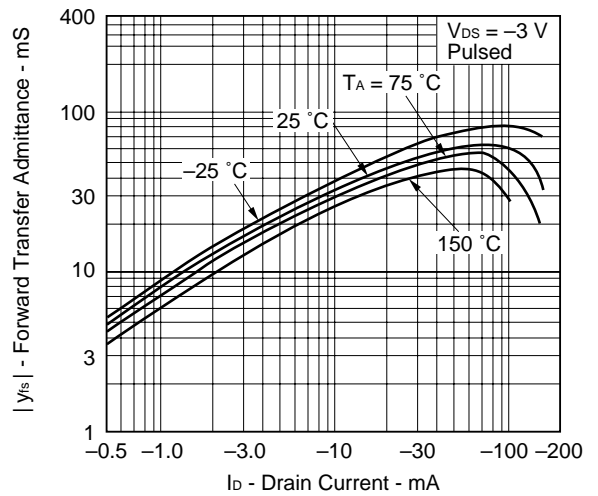
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



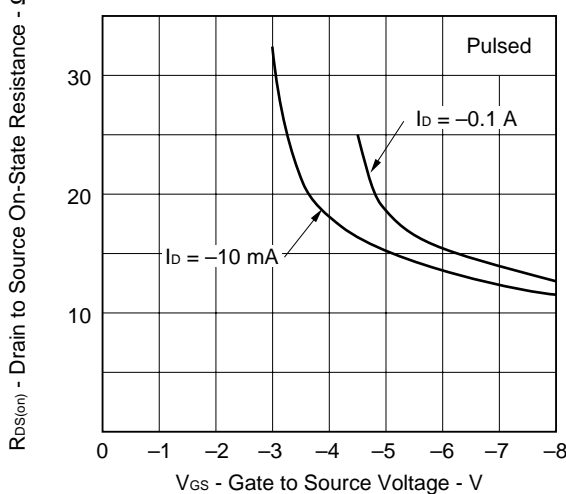
TRANSFER CHARACTERISTICS



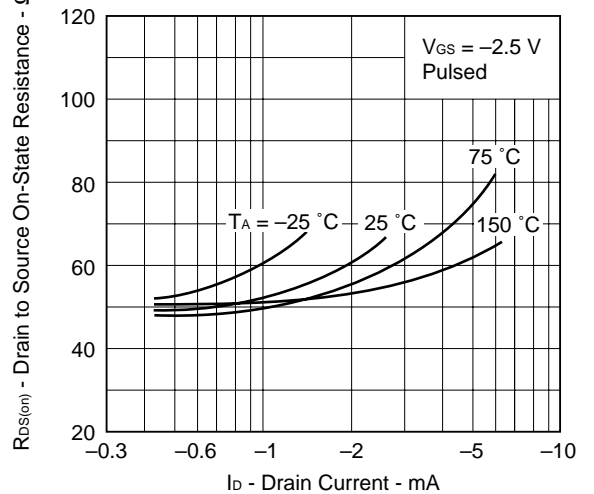
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT

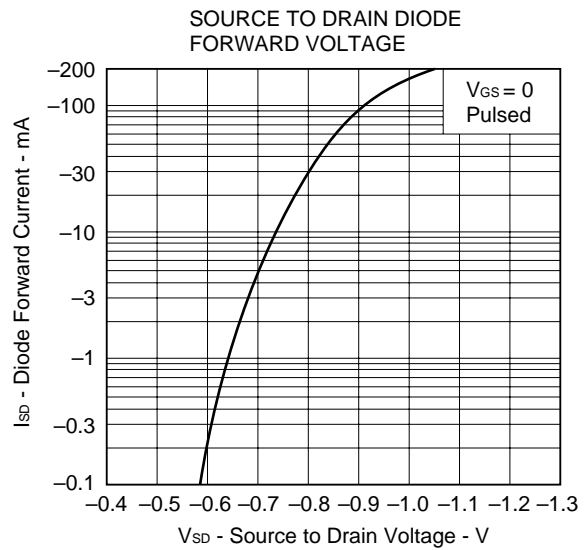
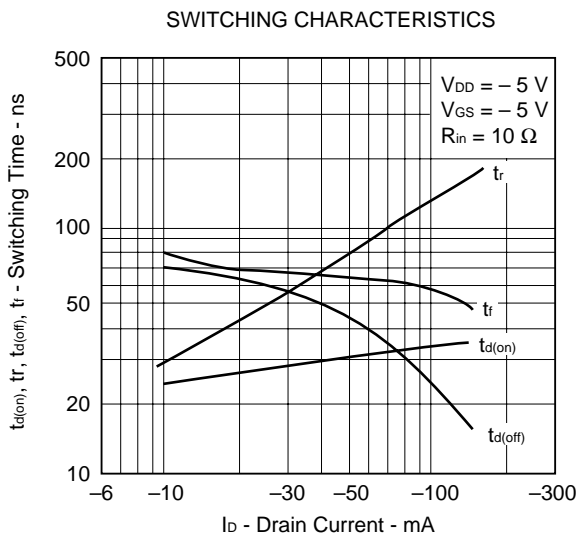
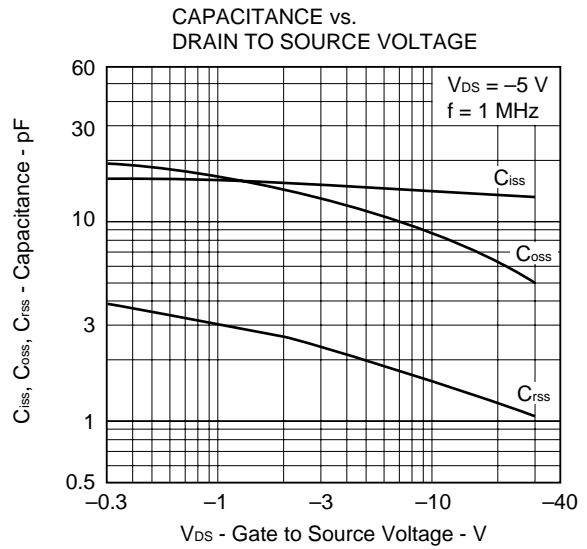
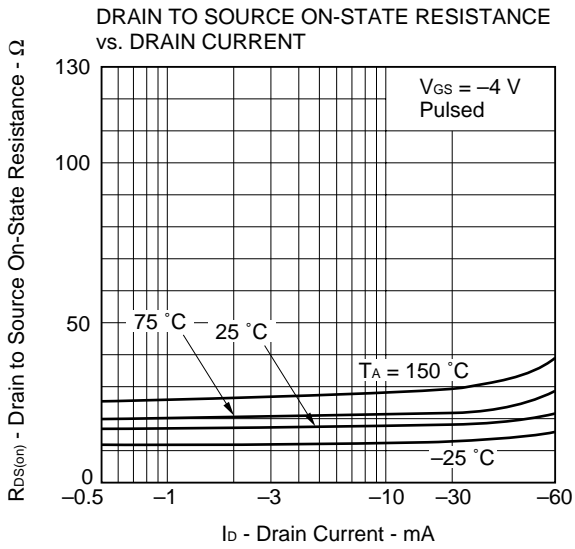


DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT





REFERENCE

Document Name	Document No.
NEC semiconductor device reliability/quality control system	TEI-1202
Quality grade on NEC semiconductor devices	IEI-1209
Semiconductor device mounting technology manual	C10535E
Guide to quality assurance for semiconductor devices	MEI-1202
Semiconductor selection guide	X10679E

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Anti-radioactive design is not implemented in this product.